

Gate oxide (35 nm SiO₂)

The diagram illustrates a cross-section of a semiconductor device. It consists of three distinct layers. The top layer is a light blue rectangle labeled 'Gate oxide (35 nm SiO₂)'. Below this is a large orange rectangle labeled 'p-type Si substrate'. At the very bottom is a thin, light blue rectangle that is not labeled. All three layers are separated by thin black horizontal lines, and the entire structure is bounded by a black frame.

p-type Si substrate